BUK9880-55A

N-channel TrenchMOS logic level FET

19 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- · Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|---|--|--|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 150 °C | | - | - | 55 | V |
| I _D | drain current | V _{GS} = 5 V; T _{sp} = 25 °C; <u>Fig. 3</u> ; <u>Fig. 2</u> | | - | - | 7 | Α |
| P _{tot} | total power dissipation | T _{sp} = 25 °C; <u>Fig. 1</u> | | - | - | 8 | W |
| Static characte | eristics | | | | | | - |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 8 A; T _j = 25 °C | | - | 62 | 73 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 8 A; T _j = 25 °C | | - | - | 89 | mΩ |
| | | $V_{GS} = 5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 13;$ Fig. 14 | | - | 68 | 80 | mΩ |
| Avalanche rug | Avalanche ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | I_D = 6 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped | | - | - | 36 | mJ |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|----------------------------|----------------|
| 1 | G | gate | 4 | D I |
| 2 | D | drain | | |
| 3 | S | source | | G—UNA) |
| 4 | D | drain | ⊟1 ⊟2 ⊟3 SC-73 (SOT223) | mbb076 S |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|----------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| BUK9880-55A | SC-73 | plastic surface-mounted package with increased heatsink; 4 leads | SOT223 | | |
| BUK9880-55A/CU | SC-73 | plastic surface-mounted package with increased heatsink; 4 leads | SOT223 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|----------------|--------------|
| BUK9880-55A | 988055A |
| BUK9880-55A/CU | 988055 |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 150 °C | - | 55 | V |
| V_{DGR} | drain-gate voltage | R_{GS} = 20 k Ω | - | 55 | V |
| V_{GS} | gate-source voltage | | -15 | 15 | V |
| P _{tot} | total power dissipation | T _{sp} = 25 °C; <u>Fig. 1</u> | - | 8 | W |
| I _D | drain current | T _{sp} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u> | - | 4 | А |
| | | T _{sp} = 25 °C; V _{GS} = 5 V; <u>Fig. 3</u> ; <u>Fig. 2</u> | - | 7 | Α |
| I _{DM} | peak drain current | T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3 | - | 30 | Α |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|-----------|-----------------|-----|------|
| T _{stg} | storage temperature | | | -55 | 150 | °C |
| Tj | junction temperature | | | -55 | 150 | °C |
| V_{GSM} | peak gate-source voltage | pulsed; t _p ≤ 50 μs | | -15 | 15 | V |
| Source-dra | in diode | | <u> </u> | | | |
| Is | source current | T _{sp} = 25 °C | | - | 7 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^{\circ}C$ | | - | 30 | Α |
| Avalanche | ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 6 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped | | - | 36 | mJ |
| E _{DS(AL)R} | repetitive drain-source avalanche energy | Fig. 4 | [1][2][3] | [4] | - | J |

- [1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 150 °C.
- [3] Repetitive avalanche rating limited by an average junction temperature of 145 °C.
- [4] Refer to application note AN10273 for further information.

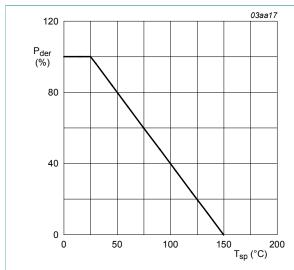


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

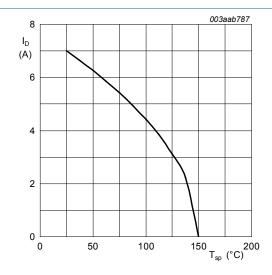


Fig. 2. Continuous drain current as a function of solder point temperature

$$V_{GS} \ge 5V$$

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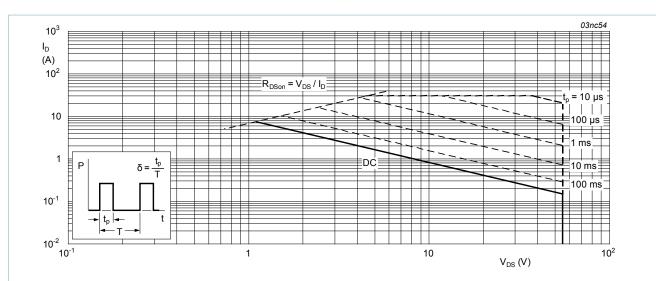


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{amb} = 25$$
° C ; I_{DM} is single pulse

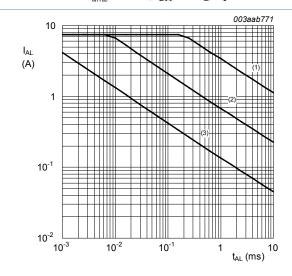


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time.

(1) Single-pulse; $T_j = 25$ °C.

(2) Single-pulse; $T_j = 125 \, ^{\circ}C$.

(3) Repetitive.

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|------|
| R _{th(j-sp)} | thermal resistance from junction to solder point | | - | - | 15 | K/W |

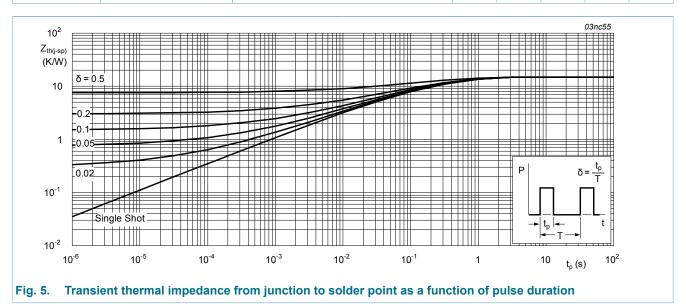
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|------------|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | Fig. 5 | - | 120 | - | K/W |



10. Characteristics

Table 7. Characteristics

| Parameter | Conditions | Min | Тур | Max | Unit |
|--|---|-----|------|-----|------|
| cteristics | | | | | |
| drain-source | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$ | 50 | - | - | V |
| breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | 55 | - | - | V |
| gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 12; Fig. 8 | 1 | 1.5 | 2 | V |
| | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 150 °C; Fig. 12; Fig. 8 | 0.6 | - | - | V |
| | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 12; Fig. 8 | - | - | 2.3 | V |
| drain leakage current | V _{DS} = 55 V; V _{GS} = 0 V; T _j = 150 °C | - | - | 500 | μΑ |
| | V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.05 | 10 | μΑ |
| gate leakage current | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} drain-source on-state resistance | V _{GS} = 5 V; I _D = 8 A; T _j = 150 °C; Fig. 13; Fig. 14 | - | - | 147 | mΩ |
| | V _{GS} = 10 V; I _D = 8 A; T _j = 25 °C | - | 62 | 73 | mΩ |
| | V _{GS} = 4.5 V; I _D = 8 A; T _j = 25 °C | - | - | 89 | mΩ |
| | drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state | | | | |

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|------------------------------|--|-----|------|-----|------|
| | | V _{GS} = 5 V; I _D = 8 A; T _j = 25 °C; <u>Fig. 13;</u> <u>Fig. 14</u> | - | 68 | 80 | mΩ |
| Dynamic c | haracteristics | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 10 A; V _{DS} = 44 V; V _{GS} = 5 V; | - | 11 | - | nC |
| Q_{GS} | gate-source charge | Fig. 11 | - | 1.6 | - | nC |
| Q_{GD} | gate-drain charge | I _D = 10 A; V _{DS} = 44 V; V _{GS} = 5 V; Fig. 15 | - | 4.6 | - | nC |
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16$ | - | 438 | 584 | pF |
| C _{oss} | output capacitance | | - | 87 | 104 | pF |
| C _{rss} | reverse transfer capacitance | | - | 62 | 85 | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$ | - | 8 | - | ns |
| t _r | rise time | $R_{G(ext)} = 10 \Omega; T_j = 25 ^{\circ}C$ | - | 118 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 20 | - | ns |
| t _f | fall time | | - | 32 | - | ns |
| Source-dra | in diode | | | | | |
| V_{SD} | source-drain voltage | I_S = 15 A; V_{GS} = 0 V; T_j = 25 °C; <u>Fig. 17</u> | - | 0.85 | 1.2 | V |
| t _{rr} | reverse recovery time | I _S = 20 A; dI _S /dt = -100 A/μs; | - | 33 | - | ns |
| Q _r | recovered charge | $V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$ | - | 60 | - | nC |

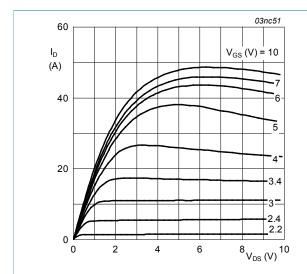


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values $T_j = 25 ^{\circ} C$

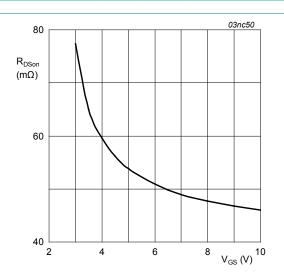


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

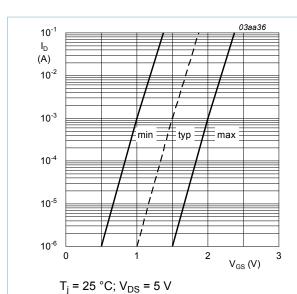


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

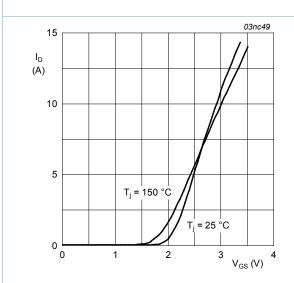


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS}=25V$$

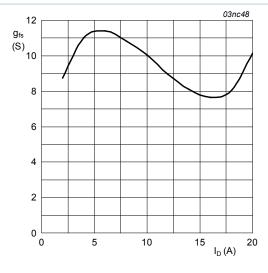


Fig. 9. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; V_{DS} = 25V$$

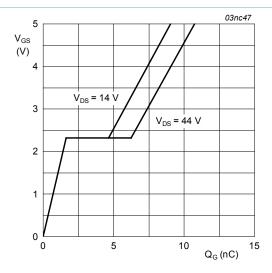


Fig. 11. Gate-source voltage as a function of turn-on gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

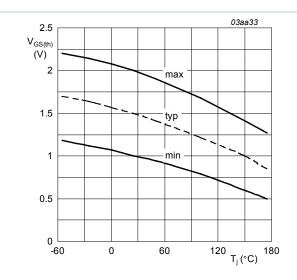


Fig. 12. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

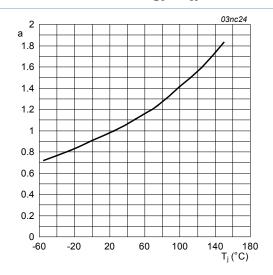


Fig. 14. Normalized drain source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

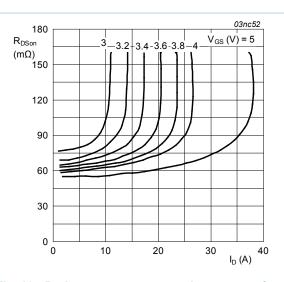


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

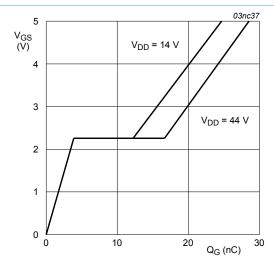


Fig. 15. Gate-source voltage as a function of turn-on gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 15A$$

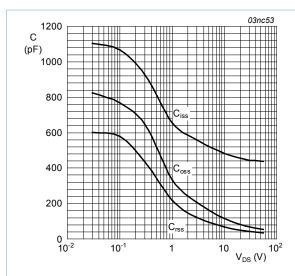
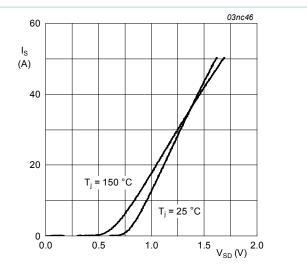


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Reverse diode current as a function of reverse as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$



diode voltage; typical value

$$V_{GS} = 0V$$

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11. Package outline

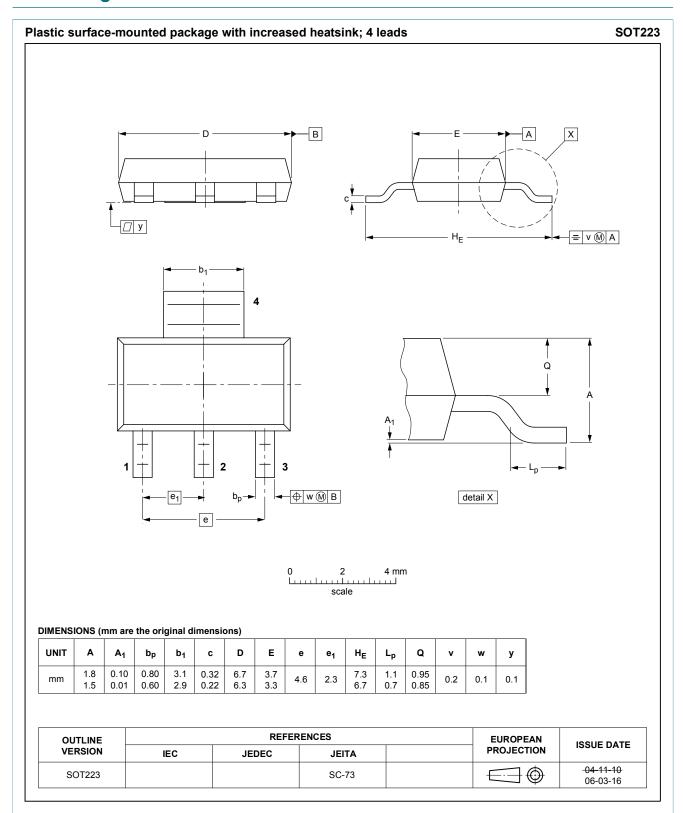


Fig. 18. Package outline SC-73 (SOT223)

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Product data sheet

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12. Legal information

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|--------------------------------------|--------------------|---|
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